

BOOK Smd General Purpose Transistor Npn Bc817 16 Bc817 25 PDF Book is the book you are looking for, by download PDF Smd General Purpose Transistor Npn Bc817 16 Bc817 25 book you are also motivated to search from other sources

### **SMD General Purpose Transistor (NPN) BC817-16/BC817-25 ...**

SMD General Purpose Transistor (NPN) Features • NPN Silicon Epitaxial Planar Transistor For Switching And Amplifier Applications • RoHS Compliance Mechanical Data Case: SOT-23, Plastic Package Terminals: Solderable Per MIL-STD-202G, Method 208 Weight: 0.008 Gram Marking Information BC817-16 BC17-25 BC817-40 Marking Code 6A 6B 6C 2th, 2024

### **BC817-40W - 45 V, 0.5 A, General Purpose NPN Transistor**

\*Date Code Orientation And/or Overbar May Vary Depending Upon Manufacturing Location. ... Safe Operating Area 1 VCE (Vdc) 0.1 1 0.1 0.01 10 100 0.01 0.001 I C (A) Single Pulse Test @ TA = 25°C Thermal Limit 100 Ms 1 S 10 Ms 1 Ms. SC-70 (SOT-323) CASE 419 ISSUE P DATE 07 OCT 2021 SCALE 4 3th, 2024

### **2N4400 & 2N4401 Silicon NPN Transistor General Purpose ...**

2N4401 40 – 500 Output Admittance Hoe IC = 1mA, VCE = 10V, F = 1kHz 1.0 – 30

µs Switching Characteristics Delay Time  $T_d$   $V_{CC} = 30V$ ,  $V_{EB} = 2V$ ,  $I_C = 150mA$ ,  
 $I_{B1} = 15mA$  – – 15 ns Rise Time  $T_r$  – – 20 ns Storage Time  $T_s$   $V_{CC} = 30V$ ,  $I_C =$   
 $150mA$ ,  $I_{B1} = I_{B2} = 15mA$  – – 225 ns Fall Time  $T_f$  – – 30 ns Note 1. Pulse Test:  
Pulse Width  $\leq \dots$  1th, 2024

### **SMD General Purpose Transistor (PNP) MMBT2907A**

Marking Code 2F - $V_{CEO}$  Collector-Emitter Voltage (Open Base) 60 V - $V_{CBO}$  Collector-  
Base Voltage (Open Emitter) 60 V - $V_{EBO}$  Emitter-Base Voltage (Open Collector) 5.0  
V - $I_C$  Collector Current (D.C) 600 mA  $P_{tot}$  Power Dissipation Above 25°C 250 mW  $f_T$   
Transition Frequency At  $F = 100MHz$  200 MHz - $I_C = 50mA$ , - $V_{CE} = 20V$  1th, 2024

### **MJE13007 Switch-mode NPN Bipolar Power Transistor**

Power Transistor For Switching Power Supply Applications The MJE13007 Is  
Designed For High-voltage, High-speed Power Switching Inductive Circuits Where  
Fall Time Is Critical. It Is Particularly Suited For 115 And 220 V Switch-mode  
Applications Such As Switching Regulators, Inverters, 3th, 2024

### **High Voltage Transistor BF393 NPN Silicon**

BF393 [Http://onsemi.com](http://onsemi.com) 3 Figure 1. DC Current Gain IC, COLLECTOR CURRENT (mA) 200 1.0 2.0 3.0 5.0 7.0 10 2 4th, 2024

### **Npn Bipolar Junction Transistor**

EE 436 BJT Currents - 9 External (terminal) Currents. All Currents Depend On V BE In Exactly The Same Way. Although It Is A Messy Exponential, They Are All Tracking Together. It Makes Sense To Look At The Ratios: Forward Current 2th, 2024

### **MPSA44 NPN High-voltage Transistor**

NXP Semiconductors Product Data Sheet NPN High-voltage Transistor MPSA44 DATA SHEET STATUS Notes 1. Please Consult The Most Recently Issued Document Before Initiating Or Completing A Design. 2. The Product Status Of Device(s) Described In This Document May Have Changed Since This Document Was Published And May Differ In Case Of Multiple Devices. 2th, 2024

### **MJE800/801/802/803 NPN Epitaxial Silicon Darlington Transistor**

©2001 Fairchild Semiconductor Corporation Rev. A1, February 2001  
MJE800/801/802/803 ... Cross-reference Search Technical Information Buy Products

Technical Support My Fairchild Company MJE800 NP 4th, 2024

### **2N4401 NPN Switching Transistor - ElectroSchematics.com**

Jul 02, 2013 · NPN Switching Transistor 2N4401 PACKAGE OUTLINE UNIT A OUTLINE REFERENCES VERSION EUROPEAN PROJECTION ISSUE DATE IEC JEDEC JEITA Mm 5.2 5.0 B 0.48 0.40 C 0.45 0.38 D 4.8 4.4 D 1.7 1.4 E 4.2 3.6 L 14.5 12.7 E 2.54 E1 1.27 L1 (1) Max. 2.5 B1 0.66 0.55 DIMENSIONS (mm Are The Original Dimensions) Note 1. Terminal Dimensions Within This Zone Are ... 1th, 2024

### **BC546/547/548/549/550 NPN Epitaxial Silicon Transistor**

Figure 5. Output Capacitance Figure 6. Current Gain Bandwidth Product 0 2468 101214161820 0 20 40 60 80 100 I B = 50 $\mu$ A I B = 100 $\mu$ A I B = 150 $\mu$ A I B = 200 $\mu$ A I B = 250 $\mu$ A I B = 300 $\mu$ A I B = 350 $\mu$ A I B = 400 $\mu$ A I C [mA], COLLECTOR CURRENT V CE [V], COLLECTOR-EMITTER VOLTAGE 0.0 0.2 0.4 0.6 0.8 1.0 1.2 0. 1th, 2024

### **NTE130 (NPN) & NTE219 (PNP) Silicon Power Transistor ...**

Silicon Power Transistor Audio Power Amp, Medium Speed Switch Description: The NTE130 (NPN) And NTE219 (PNP) Are Silicon Complementary Transistors In A TO3

Type Case Designed For General Purpose Switching And Amplifier Applications.  
Features: DC Current Gain:  $HFE = 20 - 70 @ IC = 4A$  Collector-Emitter Saturation  
Voltage:  $VCE(sat) = 1.1V$  (Max ... 3th, 2024

### **MJE340 - Plastic Medium-Power NPN Silicon Transistor**

0.01 0.03 1.0 2.0 5.0 10 20 50 100 2000.1 0.50.2 1.0 0.2 0.1 R(t), Effective  
Transient 0.05  $Jc(t) = R(t) Jc Jc = 3.12^{\circ}C/W$  Max D Curves Apply For Power Pulse  
Train Shown Read Time At T1 ... Asme Y14.5m, 1994. 2. Controlling Dimension:  
Millimeters. 3. Number And Shape Of Lugs Optional. 2x 2x Q D L1 P B2 B E C L A1 A  
Front View Back View Front ... 1th, 2024

### **PBSS4140DPN 40 V Low V CEsat NPN/PNP Transistor**

2001 Dec 13 5 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN/PNP  
Transistor PBSS4140DPN Handbook, Halfpage 0 1000 200 400 600 800 MLD642  
10-1 1 (1) 10 IC (mA) HFE 102 103 104 3th, 2024

### **PBSS4140U 40 V Low V CEsat NPN Transistor - Nexperia**

2001 Jul 13 4 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN

Transistor PBSS4140U Handbook, Halfpage 0 1000 200 400 600 800 MLD660 10–1  
1 (1) 10 IC (mA) HFE 102 103 104 3th, 2024

**NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor**

NSS20201LT1G, NSV20201LT1G [www.onsemi.com](http://www.onsemi.com) 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A 3th, 2024

**NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor**

Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above 25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient R JA (Note 1) 143 °C/W Total Device Dissipation, TA 1th, 2024

**MPS5179 / MMBT5179 / PN5179 NPN RF Transistor**

Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia

TNR 13" Qty Per Reel/Tube/Bag 3,000 10,000 Box Dimension (mm) 187x107x183  
343x343x64 Max Qty Per Box 24,000 30,000 Weight Per Unit (gm) 0.0082 0.0082  
Weight Per Reel (kg) 0.1175 0.4006 Human ... 3th, 2024

### **TOSHIBA Transistor Silicon NPN Tr Iple Diffused Type (PCT ...**

Mar 10, 2010 · Plasma Display, Nixie Tube Driver Applications Cathode Ray Tube  
Brightness Control Applications • High Breakdown Voltage: VCBO = 300 V, ... 12 14  
0.6 2 0.5 0.4 0.3 0.2 50 90 80 12 0 0 10 8 2 80 120 160 Common Emitter Ta = 25°C  
70 IB = 10 μA 20 2th, 2024

### **2N4401/MMBT4401 NPN General Purpose Amplifier**

2N4401 \*MMBT4401 PD Total Device Dissipation Derate Above 25°C 625 5.0 350  
2.8 MW MW/°C RθJC Thermal Resistance, Junction To Case 83.3 °C/W RθJA Thermal  
Resistance, Junction To Ambient 200 357 °C/W 2N4401 / MMBT4401 C B E TO-92 C  
B E SOT-23 Mark: 2X \*Device Mounted On FR-4 PCB 1.6" X 1.6" X 0.06." Discrete  
POWER & Signal Technologies 2th, 2024

### **Small Signal General Purpose Transistors (NPN) 2N4400/2N4401**

2N4400/2N4401 Small Signal General Purpose Transistors (NPN )  
Www.taitroncomponents.com Page 2 Of 4 Electrical Characteristics (T  
Ambient=25°C Unless Noted Otherwise) 2N4400 2N4401 Symbol Description Min.  
Max. Min. Max. Unit Conditions V(BR)CBO Collector-Base Breakdown Voltage 60 - 60  
- V IC=100µA, IE=0 3th, 2024

### **2N4401, MMBT4401 - NPN General-Purpose Amplifier**

2N4401 / MMBT4401 Rev. 1.1.0 November 2014 2N4401 / MMBT4401 NPN General-  
Purpose Amplifier Ordering Information Figure 1. 2N4401 Device Package Figure 2.  
MMBT4401 Device Package Part Number Marking Package Packing Method  
2N4401BU 2N4401 TO-92 3L Bulk 2N4401TF 2N4401 TO-92 3L Tape And Reel  
2N4401TFR 2N4401 TO-92 3L Tape And Reel 2N4401TA 2N4401 ... 3th, 2024

### **LOW FREQUENCY SMD CRYSTAL LOW FREQUENCY SMD ...**

LOW FREQUENCY SMD CRYSTAL LOW FREQUENCY SMD CRYSTAL LOW FREQUENCY  
SMD CRYSTAL STANDARD SPECIFICATIONS: OUTLINE DRAWING: MARKING  
INSTRUCTIONS: OPTIONS AND PART IDENTIFICATION (Left Blank If Standard): 8.0 X  
3.8 X 2.5mm TABLE 1: 20.000 To 27.000 (Fund) 30 9.000 To 12.999 (Fund) 60



13.000 To 15.999 ... 3th, 2024

### **Smd Transistor Code Wordpress**

Size Chart - Footprint Selection Chart - TopLine Dummy 40 V, 200 MA NPN Switching Transistor 5 November 2020 Product Data Sheet 1. General Description NPN Switching Transistor In A Small SOT23 (TO-236AB) Surface-Mounted 4th, 2024

### **Smd Transistor Marking Code Pdf - Mbmwebsite.com**

SMD Code Book And Marking Codes - ElectroSchematics.com Next Look Up The Code In The Alphanumeric Listing Which Forms The Main Part Of The Pdf Book By Looking For The First Character In The Left Column. You Can Use The CTRL + F Shortcut To Search For A ... 1th, 2024

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